

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	59756	(crystal\$10 near10 orientation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:05
L2	1396	(crystal\$10 near10 orientation) with semiconductor with layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:05
L3	136	(crystal\$10 near10 orientation) with semiconductor with layer with (conduct\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:06
L4	50	(crystal\$10 near10 orientation) near10 semiconductor near5 layer near10 (conduct\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:06
L5	23	(first or second or third or different) near5 (crystal\$10 near10 orientation) near10 semiconductor near5 layer near10 (conduct\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:07
L6	12	(first or second or third or different) near (crystal\$10 near10 orientation) near10 semiconductor near5 layer near10 (conduct\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:07
L7	8	(first or second or third or different) near (crystal\$10 near5 orientation) near10 semiconductor near5 layer near10 (conduct\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:18
L8	0	"2000582531"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:10
L9	0	"200582531"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:10

L21		3	((semiconductor adj layer) near10 ((first or second or different) near (crystal\$10 near orientation)) near10 (conduct\$5 near interface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:26
L22		3	((semiconductor adj layer) near10 ((first or second or different) near (crystal\$10 near orientation)) near10 (conduct\$5 near5 interface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:26
L23		3	((semiconductor adj layer) with ((first or second or different) near (crystal\$10 near orientation)) near10 (conduct\$5 near5 interface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:27
L24		3	((semiconductor adj layer) with ((first or second or different) near (crystal\$10 near orientation)) with (conduct\$5 near5 interface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:28
L25		3	((semiconductor adj layer) with ((first or second or different) near5 (crystal\$10 near orientation)) with (conduct\$5 near5 interface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:27
L26		3	((semiconductor) with ((first or second or different) near5 (crystal\$10 near orientation)) with (conduct\$5 near5 interface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:27
L27		64	((semiconductor) with ((first or second or different) near5 (crystal\$10 near orientation)) with (conduct\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:27
L28		6	((semiconductor adj layer) with ((first or second or different) near (crystal\$10 near orientation)) with (conduct\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:28
L30		45	((first or second or different) near (crystal\$10 near orientation)) near10 (conduct\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:31
L31		4	((first or second or different) near (crystal\$10 near orientation)) near10 (conduct\$5) near10 (interface or between or separa\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:30

L32	29	((first or second or different) near (crystal\$10 near orientation)) near10 (interface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:56
L33	4	((first or second or different) near (crystal\$10 near orientation)) near10 (interface)) and (interface near10 (conduct\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:58
L34	29	((first or second or different) near (crystal\$10 near orientation)) near10 (interface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:58
L35	8	((first or second or different) near semiconductor near10 (crystal\$10 near orientation)) near10 (interface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:00
L36	6	((first or second or different) near semiconductor near layer near10 (crystal\$10 near orientation)) near10 (interface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:03
L37	42	((first or second or different) near semiconductor near layer near10 (crystal\$10 near orientation)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:03
L38	7	((first or second) near semiconductor near layer near10 (different near crystal\$10 near orientation)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:04
L39	10	((first or second or upper or lower or top or bottom) near semiconductor near layer near10 (different near crystal\$10 near orientation)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:07
L40	6	((first or second or upper or lower or top or bottom) near semiconductor near layer near10 (different near crystal\$10 near orientation))) and interface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:11
L41	2	((first or second or upper or lower or top or bottom) near semiconductor near layer near10 (different near crystal\$10 near orientation))) and (conduct\$5 near2 interface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:12

L42	43	(semiconductor adj layer) and (crystal\$10 near orientation) and (conduct\$5 near interface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:16
L43	5	(semiconductor adj layer) same (crystal\$10 near orientation) and (conduct\$5 near interface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:16
L44	4	(semiconductor adj layer) same (crystal\$10 near orientation) same (conduct\$5 near interface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:17
L45	4	(semiconductor adj layer) same (crystal\$10 near orientation) same (conduct\$5 near2 (between or separat\$5 or interface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:18
L46	702	(semiconductor adj layer) same (crystal\$10 near orientation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:18
L47	323	(semiconductor adj layer) with (crystal\$10 near orientation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:18
L48	27	(semiconductor adj layer) with (crystal\$10 near orientation) with (conduct\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:20
L49	19	(semiconductor adj layer) with (different near crystal\$10 near orientation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:24
L50	3	(semiconductor adj layer) with (different near crystal\$10 near orientation) with interface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:25
L51	4	(semiconductor adj layer) with (different near crystal\$10 near orientation) with (conduct\$5 or interface or between or separat\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:31

L52	5	(semiconductor adj layer) same (different near crystal\$10 near orientation) with (conduct\$5 or interface or between or separat\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:31
L53	14	(semiconductor adj layer) same (different near crystal\$10 near orientation) same (conduct\$5 or interface or between or separat\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 19:35
L54	18	(semiconductor adj layer) near10 (different near crystal\$10 near orientation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 20:00
L55	2	"20040195646"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 20:03
L56	2	"20040075141"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 20:03
L57	4	I55 or I56	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 20:03
L58	1	I57 and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 20:03